

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 240438US2		SERIAL NO. New Application	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT		10/620,379	
				Hirokazu SAYAMA, et al.			
				FILING DATE		GROUP	
		Herewith					
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	AA	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE
	AB						
	AC						
	AD						
	AE						
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						
	AL						
	AM						
	AN						
FOREIGN PATENT DOCUMENTS							
		DOCUMENT NUMBER	DATE	COUNTRY	TRANSLATION YES NO		
<div style="font-size: 1.5em;"> <i>DL</i> <i>DL</i> </div>	AO	2002-93921	03/29/02	Japan (with English extract)		X	
	AP	2001-284558	10/12/01	Japan (with English extract)		X	
	AQ						
	AR						
	AS						
	AT						
	AU						
	AV						
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
<div style="font-size: 1.5em;"> <i>DL</i> <i>DL</i> </div>	AW	J. WELSER, et al., "NMOS AND PMOS TRANSISTORS FABRICATED IN STRAINED SILICON/RELAXED SILICON-GERMANIUM STRUCTURES", Proc. of International Electron Device Meeting 1992, IEDM 92, pgs. 1000 - 1002.					
	AX	T. MIZUNO, et al., "HIGH PERFORMANCE STRAINED-Si p-MOSFETs ON SiGe-ON-INSULATOR SUBSTRATES FABRICATED BY SIMOX TECHNOLOGY", Proc. of International Electron Device Meeting 1999, IEEE, pgs. 934 - 936.					
	AY						
	AZ						
					<input type="checkbox"/> Additional References sheet(s) attached		
Examiner <i>DL</i>					Date Considered <i>9/15/04</i>		
<small>*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</small>							